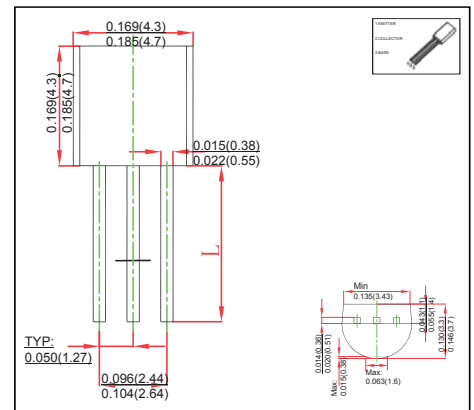


TO-92 Plastic-Encapsulate Transistors
FEATURE

- Power Switching Applications
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	600	V
Collector-Emitter Voltage	VCEO	400	V
Emitter-Base Voltage	VEBO	6	V
Collector Current -Continuous	IC	0.8	A
Collector Power Dissipation	PC	0.9	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55 ~ 150	°C

 Electrical Specification ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	$I_C=100\mu\text{A}, I_E=0$	600			V
Collector-emitter breakdown voltage	V(BR)CEO	$I_C=1\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	V(BR)EBO	$I_C=1\text{mA}, I_B=0$	6			V
Collector cut-off current	ICBO	$V_{CB}=600\text{V}, I_E=0$			100	μA
	ICEO	$V_{CB}=400\text{V}, I_B=0$			100	μA
Emitter cut-off current	IEBO	$V_{EB}=6\text{V}, I_C=0$			100	μA
DC current gain	hFE1	$V_{CE}=10\text{V}, I_C=200\text{mA}$			40	
	hFE2	$V_{CE}=10\text{V}, I_C=0.025\text{mA}$				
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200\text{mA}, I_B=40\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=200\text{mA}, I_B=40\text{mA}$			1.1	V
Transition frequency	fT	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=1\text{MHz}$	5			MHz
Fall time	tf	$I_C=1\text{A}, I_{B1}=-I_{B2}=0.2\text{A}$			0.5	μs
Storage time	ts	$V_{CC}=100\text{V}$			2.5	μs

RATINGS AND CHARACTERISTIC CURVES

